



LGE3M30065B

Silicon Carbide Power MOSFET



$V_{DS} = 650\text{ V}$
 $I_D@25^\circ\text{C} = 91\text{ A}$
 $R_{DS(ON)} = 30\text{ m}\Omega$

Features

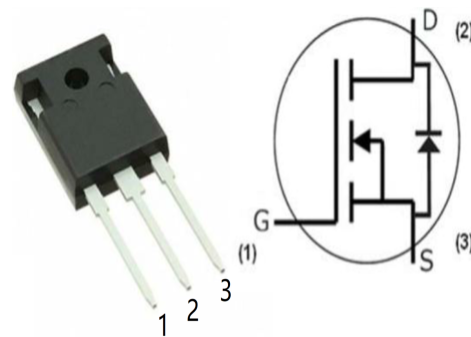
- High Blocking Voltage
- High Frequency Operation
- Low on-resistance
- Fast intrinsic diode with low reverse recovery

Benefits

- Higher System Efficiency
- Parallel Device Convenience without thermal runaway
- High Temperature Application
- Hard Switching & Higher Reliability
- Easy to drive

Applications

- Motor Drives
- Solar / Wind Inverters
- Onboard EV Charger
- Energy Storage
- Server
- Telecom
- SMPS
- Uninterruptable power supplies



TO-247-3
Pin definition

Part Number	Package	Marking
LGE3M30065B	TO-247-3	LGE3M30065B

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handing procedures.



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Maximum Ratings

$T_C=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Test conditions	Value	Unit
Drain - Source Voltage	V_{DSmax}	$V_{GS}=0\text{V}$, $I_D=100\mu\text{A}$	650	V
Gate - Source Voltage (dynamic)	V_{GSmax}	AC ($f>1\text{ Hz}$)	-10/+25	V
Gate - Source Voltage (static)	V_{GSop}	static	-5/+20	V

Maximum Ratings

$T_C=25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous Drain Current: $V_{GS} = 20\text{V}$ $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_D	91 64	A
Pulsed Drain Current: $T_C=25^{\circ}\text{C}$	$I_{D(pulse)}$	212	A
Short Circuit Capability : $V_{DD} = 400\text{V}$ $V_{GS} = 20\text{V}$	t_{sc}	10	μS
Short Circuit Capability : $V_{DD} = 400\text{V}$ $V_{GS} = 20\text{V}$	I_{DS}	400	A
Total power dissipation : $T_C = 25^{\circ}\text{C}$	P_D	326	W
Operating Junction Temperature :	T_J	-55 to 175	$^{\circ}\text{C}$
Storage Temperature :	T_{STG}	-55 to 150	$^{\circ}\text{C}$

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Thermal Characteristics

Parameter	Symbol	Condition	Typ	Max	Unit
Thermal Resistance (per device)	Rth(j-c)	junction-case	0.37	0.46	°C/W

Electrical Characteristic

$T_c = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	650			V	$V_{GS} = 0V, I_D = 100\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	2.0	3.0 2.2 2.0	4.0	V	$V_{DS} = V_{GS}, I_D = 10mA$ $T_J = 150^\circ\text{C}$ $T_J = 175^\circ\text{C}$
Zero Gate Voltage Drain Current	I_{DSS}	0	1	100	μA	$V_{DS} = 650V, V_{GS} = 0V$
Gate-Source Leakage Current	I_{GSS}	0 -200	10 -10	200 0	nA	$V_{GS} = 20V, V_{DS} = 0V$ $V_{GS} = -5V, V_{DS} = 0V$
Drain-Source On-State Resistance	$R_{DS(on)}$		55 41 42		m Ω	$V_{GS} = 15V, I_D = 40 A$ $T_J = 150^\circ\text{C}$ $T_J = 175^\circ\text{C}$
			30 33 35	36		$V_{GS} = 20V, I_D = 40 A$ $T_J = 150^\circ\text{C}$ $T_J = 175^\circ\text{C}$
Transconductance	g_{fs}		21 20 19		S	$V_{DS} = 20V, I_D = 40 A$ $T_J = 150^\circ\text{C}$ $T_J = 175^\circ\text{C}$
Input capacitance	C_{iss}		2940		pF	$V_{DS} = 400V$ $V_{GS} = 0V$ $f = 1MHz$
Output capacitance	C_{oss}		280			
Reverse transfer capacitance	C_{rss}		14			
C_{oss} Stored Energy	E_{oss}		28			

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Total gate charge	Q_g		147		nC	$V_{DS} = 400V$ $V_{GS} = -5V / 20V$ $I_D = 40 A$
Gate-source charge	Q_{gs}		45			
Gate-drain charge	Q_{gd}		63			
Internal gate input resistance	$R_{g(int)}$		2.0		Ω	$f = 1MHz, I_D = 0A$
Turn-On Switching Energy	E_{ON}		209		μJ	$V_{DS} = 400V$ $V_{GS} = -5V/20V$ $I_D = 40A, R_{G(ext)} = 2 \Omega$ $L = 200\mu H$
Turn-Off Switching Energy	E_{OFF}		39			
Turn-On Delay Time	$t_{d(on)}$		13		ns	
Rise Time	t_r		30			
Turn-Off Delay Time	$t_{d(off)}$		29			
Fall Time	t_f		6			
Avalanche Capability	E_{AS}		338		mJ	
	I_A		26		A	

Reverse Diode Characteristics

$T_C = 25^\circ C$, unless otherwise specified

Parameter	Symbol	Value			Unit	Test Condition
		Min.	Typ.	Max.		
Diode Forward Voltage	V_{SD}		4.1 3.7 3.6		V	$V_{GS} = -5V$ $I_{SD} = 20A$ $T_J = 150^\circ C$ $T_J = 175^\circ C$
Continuous Diode Forward Current	I_S		62		A	$V_{GS} = -5V$
Reverse Recovery time	t_{rr}		24		ns	$V_{GS} = -5V$ $I_{SD} = 40A$ $V_R = 400V$ $di/dt = 4000 A/\mu s$
Reverse Recovery Charge	Q_{rr}		345		nC	
Peak Reverse Recovery Current	I_{rrm}		23		A	

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Typical Performanc

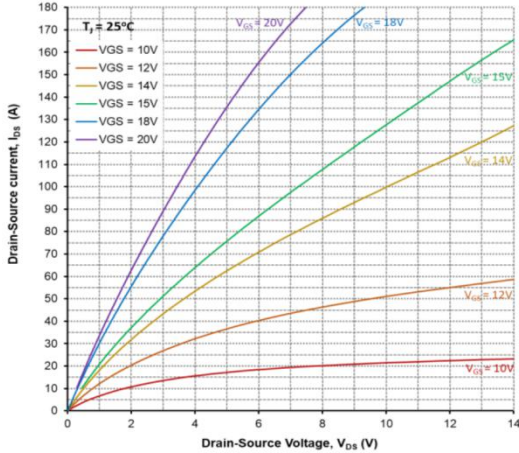


Figure 1. Output Characteristics, $T_J = 25^\circ\text{C}$

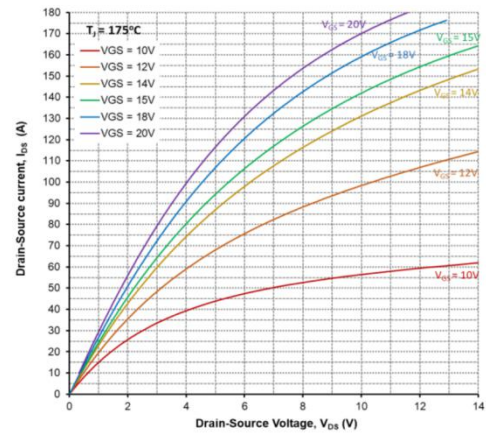


Figure 2. Output Characteristics, $T_J = 175^\circ\text{C}$

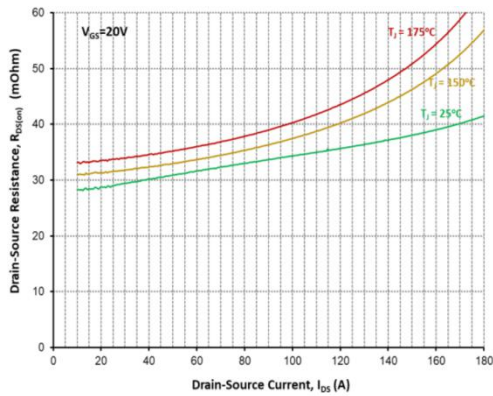


Figure 3. On-Resistance vs. Drain Current For Various Temperatures

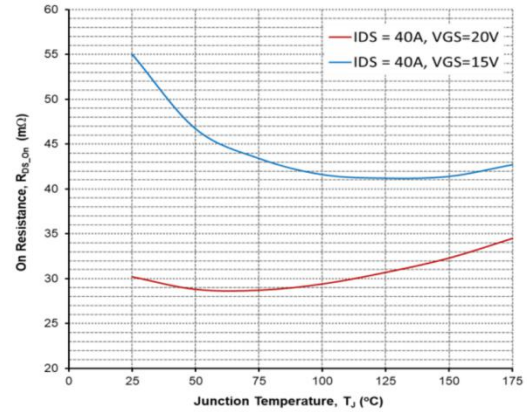


Figure 4. On-Resistance vs. Temperature

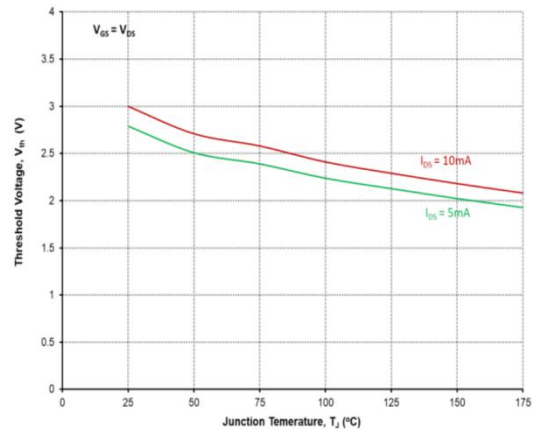
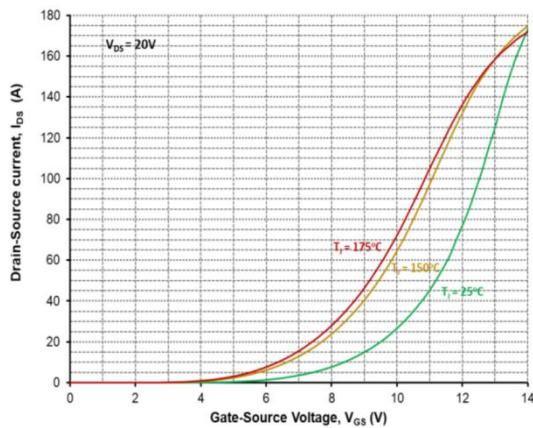


Figure 6. Threshold Voltage vs. Temperature

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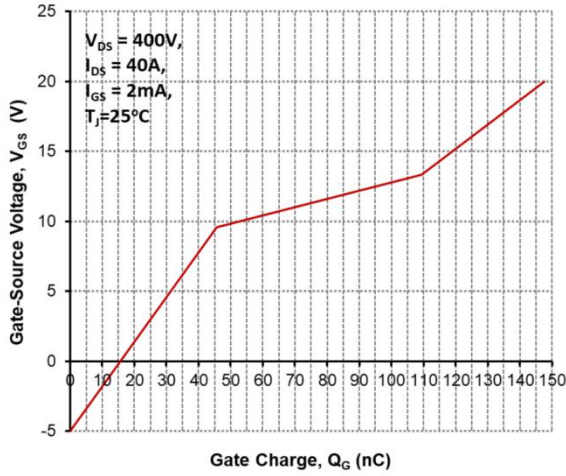


Figure 7. Gate Charge Characteristics

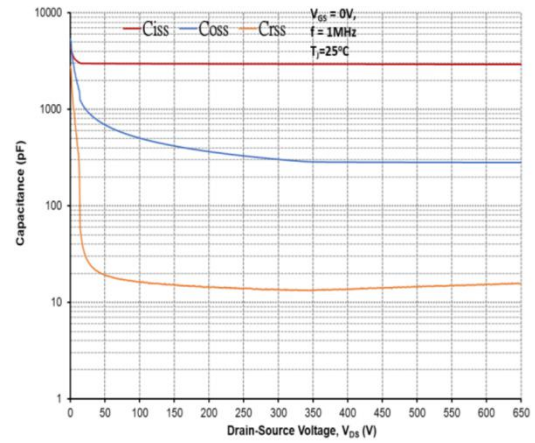


Figure 8. Capacitances vs. Drain-Source Voltage (0-650V)

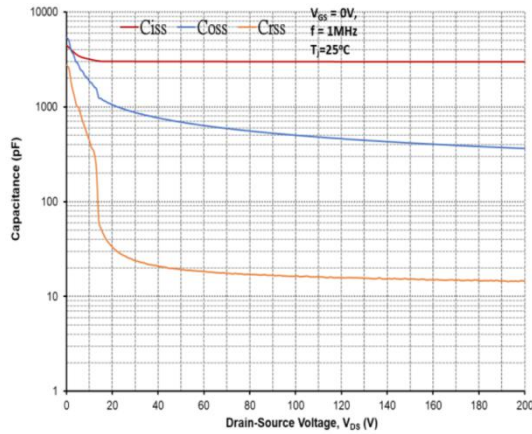


Figure 9. Capacitances vs. Drain-Source Voltage (0-200V)

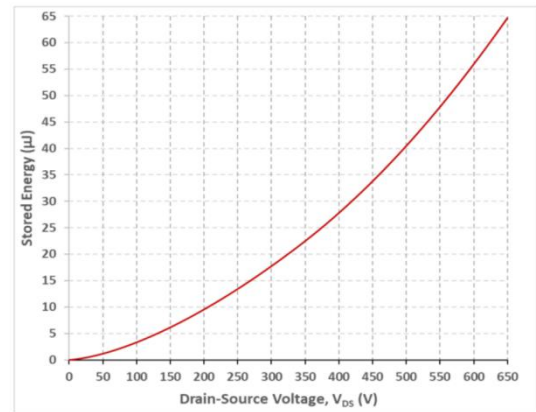


Figure 10. Output Capacitor Stored Energy

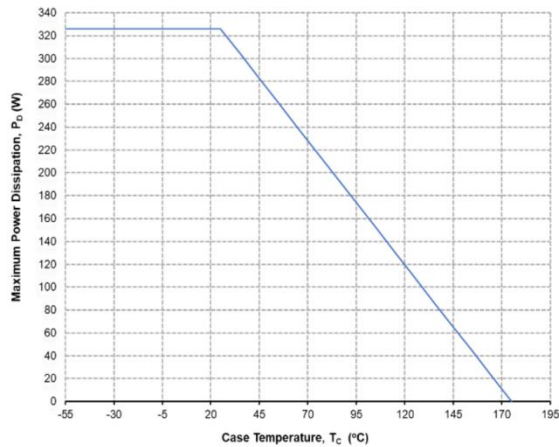


Figure 11. Maximum Power Dissipation Derating vs. Case Temperature

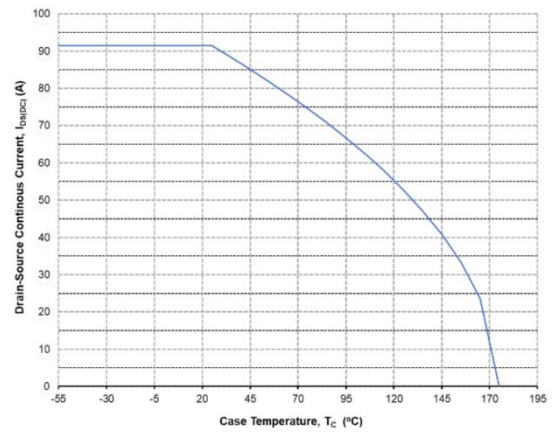


Figure 12. Continuous Drain Current Derating vs. Case Temperature

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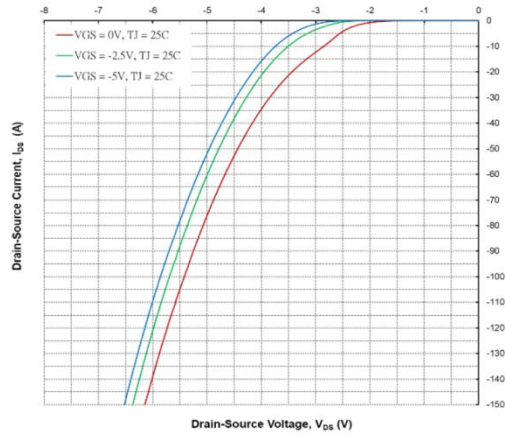


Figure 13. Body Diode Characteristics @ 25°C

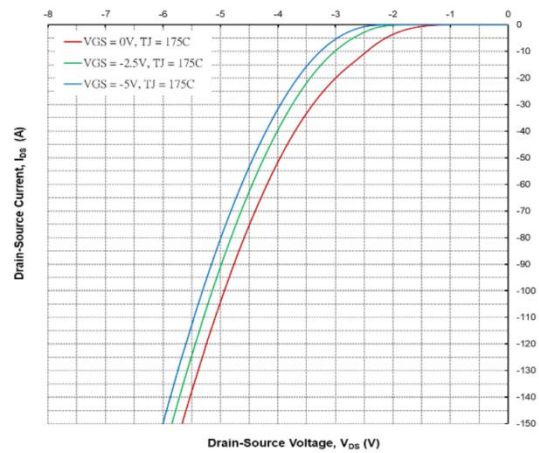


Figure 14. Body Diode Characteristics @ 175°C

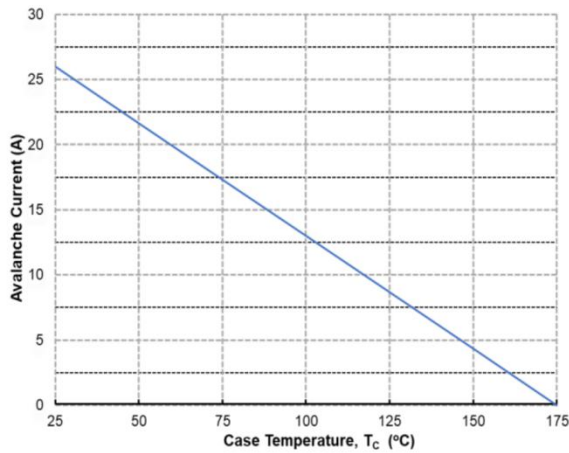


Figure 15. Single Avalanche vs. Temperature

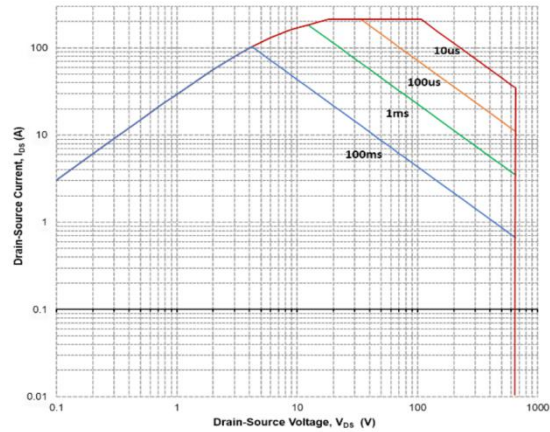
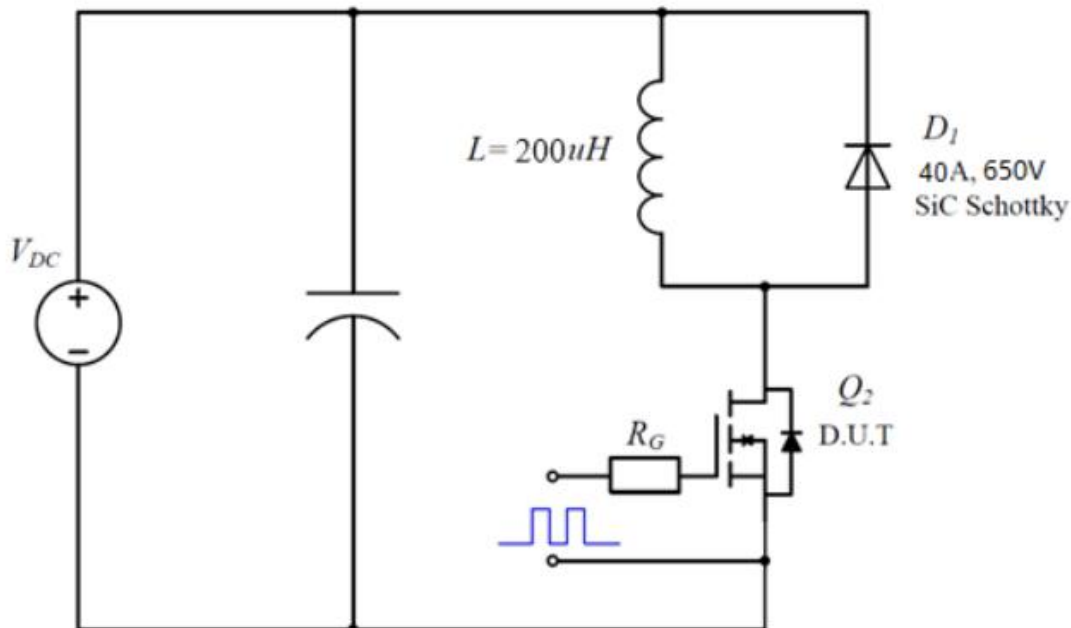
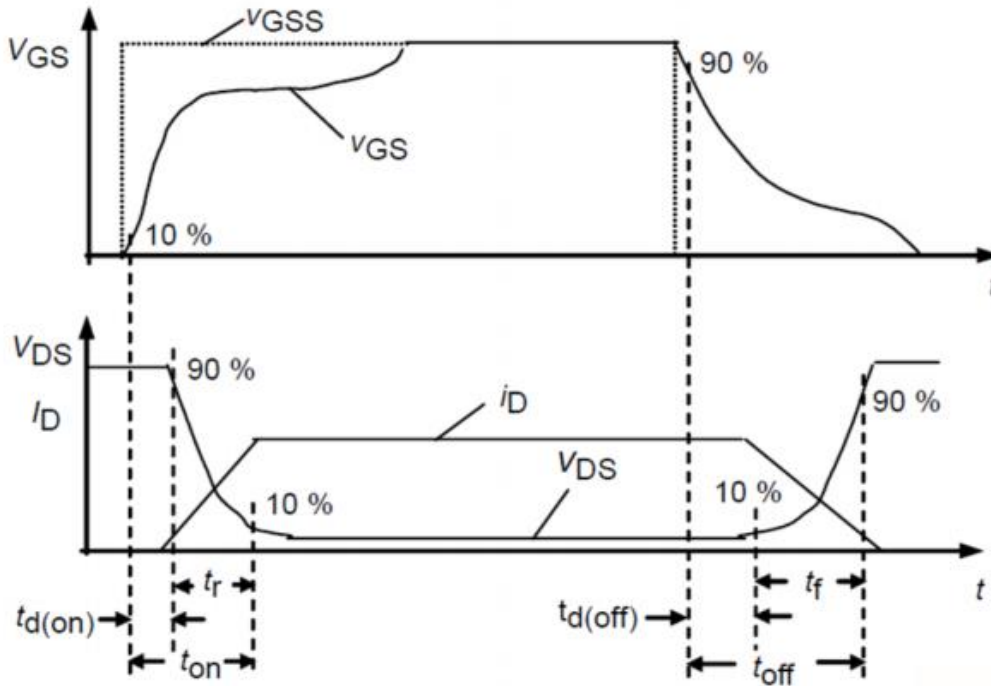


Figure 16. Safe Operating Area

Caution: This device is sensitive to electrostatic discharge .Users should follow ESD handling procedures.

Switching Times Definition and Test Circuit



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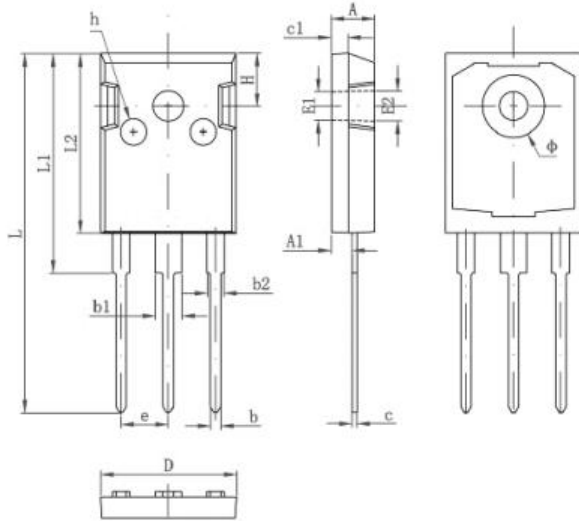
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Package Outline:TO-247-3

(TO-247-3 Package)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.850	5.150	0.191	0.200
A1	2.200	2.600	0.087	0.102
b	1.000	1.400	0.039	0.055
b1	2.800	3.200	0.110	0.126
b2	1.800	2.200	0.071	0.087
c	0.500	0.700	0.020	0.028
c1	1.900	2.100	0.075	0.083
D	15.450	15.750	0.608	0.620
E1	3.500 REF		0.138 REF	
E2	3.600 REF		0.142 REF	
L	40.900	41.300	1.610	1.626
L1	24.800	25.100	0.976	0.988
L2	20.300	20.600	0.799	0.811
Φ	7.100	7.300	0.280	0.287
e	5.450 TYP		0.215 TYP	
H	5.980 REF		0.235 REF	
h	0.000	0.300	0.000	0.012

Package	Packing	Box Size L×W×H(mm)	Quantity(pcs/box)	Carton Size L×W×H(mm)	Quantity(pcs/carton)
TO-247	30pcs/Tube	570×155×50	450	580×340×125	1800

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